

Silicon NPN Power Transistors

2SD627

DESCRIPTION

- With TO-3 package
- High voltage,high speed

APPLICATIONS

- For use in horizontal deflection output stages for color TV receivers

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

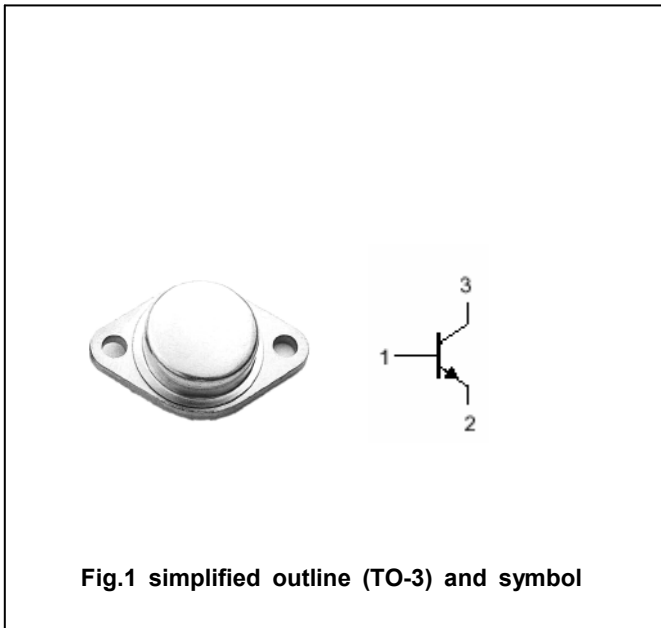


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	600	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		3	A
I _{CM}	Collector current-peak		6	A
P _C	Collector power dissipation	T _C =25□	50	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-45~150	□

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =100mA ; I _B =0	600			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2.5A; I _B =0.6A			10	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2.5A; I _B =0.6A			1.6	V
I _{CBO}	Collector cut-off current	V _{CB} =1000V; I _E =0			50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =10V	5		25	
t _f	Fall time	I _{CP} =2.5A			1.0	μs

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)